

OptiMOS™-P Power-Transistor

Features

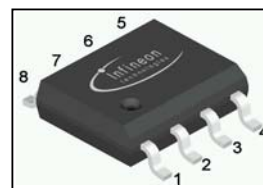
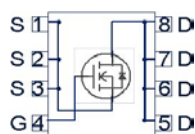
- P-Channel
- Enhancement mode
- Logic level
- 150°C operating temperature
- Qualified according JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21



Product Summary

V_{DS}	-30	V
$R_{DS(on),max}$	8	mΩ
I_D	-14.9	A

PG-DSO-8



Type	Package	Marking	lead free	Halogen free	packing
BSO080P03S H	P-DSO-8	080P3S	Yes	Yes	dry

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value		Unit
			≤10 secs	steady state	
Continuous drain current	I_D	$T_A=25\text{ °C}^{(1)}$	-14.9	-12.6	A
		$T_A=70\text{ °C}^{(1)}$	-11.9	-10	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ °C}^{(2)}$	-60		
Avalanche energy, single pulse	E_{AS}	$I_D=-14.9\text{ A}$, $R_{GS}=25\text{ Ω}$	248		mJ
Gate source voltage	V_{GS}		±25		V
Power dissipation	P_{tot}	$T_A=25\text{ °C}^{(1)}$	2.5	1.79	W
Operating and storage temperature	T_j , T_{stg}		-55 ... 150		°C
ESD class		JESD22-A114 HBM			
Soldering temperature			260		
IEC climatic category; DIN IEC 68-1			55/150/56		

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - soldering point	R_{thJS}		-	-	35	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint, $t_p \leq 10$ s	-	-	110	
		minimal footprint, steady state	-	-	150	
		6 cm ² cooling area ¹⁾ , $t_p \leq 10$ s	-	-	50	
		6 cm ² cooling area ¹⁾ , steady state	-	-	70	

Electrical characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = -250 \mu\text{A}$	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	-1	-1.5	-2.2	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -30$ V, $V_{GS} = 0$ V, $T_j = 25^\circ\text{C}$	-	-0.1	-1	μA
		$V_{DS} = -30$ V, $V_{GS} = 0$ V, $T_j = 150^\circ\text{C}$	-	-10	-100	
Gate-source leakage current	I_{GSS}	$V_{GS} = -25$ V, $V_{DS} = 0$ V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = -10$ V, $I_D = -14.9$ A	-	6.7	8.0	
Transconductance	g_{fs}	$ V_{DS} > 2 I_D R_{DS(on)max}$, $I_D = -14.9$ A	22	43	-	S

¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V},$ $V_{DS}=-25\text{ V}, f=1\text{ MHz}$	-	4430	5890	pF
Output capacitance	C_{oss}		-	1180	1570	
Reverse transfer capacitance	C_{rss}		-	970	1500	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-15\text{ V},$ $V_{GS}=-10\text{ V},$ $I_D=-1\text{ A}, R_G=6\ \Omega$	-	15	23	ns
Rise time	t_r		-	22	33	
Turn-off delay time	$t_{d(off)}$		-	130	195	
Fall time	t_f		-	110	165	

Gate Charge Characteristics³⁾

Gate to source charge	Q_{gs}	$V_{DD}=-24\text{ V},$ $I_D=-14.9\text{ A},$ $V_{GS}=0\text{ to }-10\text{ V}$	-	-11	-15	nC
Gate charge at threshold	$Q_{g(th)}$		-	-7.1	-9.5	
Gate to drain charge	Q_{gd}		-	-35		
Switching charge	Q_{sw}		-	-40	-59	
Gate charge total	Q_g		-	-102	-136	
Gate plateau voltage	$V_{plateau}$		-	-2.5	-	V
Output charge	Q_{oss}	$V_{DD}=-15\text{ V}, V_{GS}=0\text{ V}$	-	-36	-48	

Reverse Diode

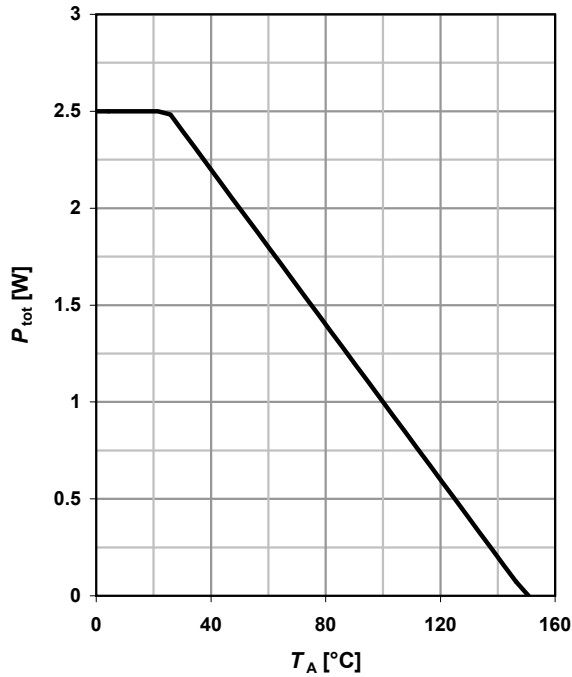
Diode continuous forward current	I_S	$T_A=25\text{ °C}$	-	-	-2.1	A
Diode pulse current	$I_{S,pulse}$		-	-	-60	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=-14.9\text{ A},$ $T_j=25\text{ °C}$	-	-0.82	-1.2	V
Reverse recovery time	t_{rr}	$V_R=15\text{ V}, I_F=-14.9\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	32	40	ns
Reverse recovery charge	Q_{rr}		-	-20	-25	nC

²⁾ See figure 3

³⁾ See figure 16 for gate charge parameter definition

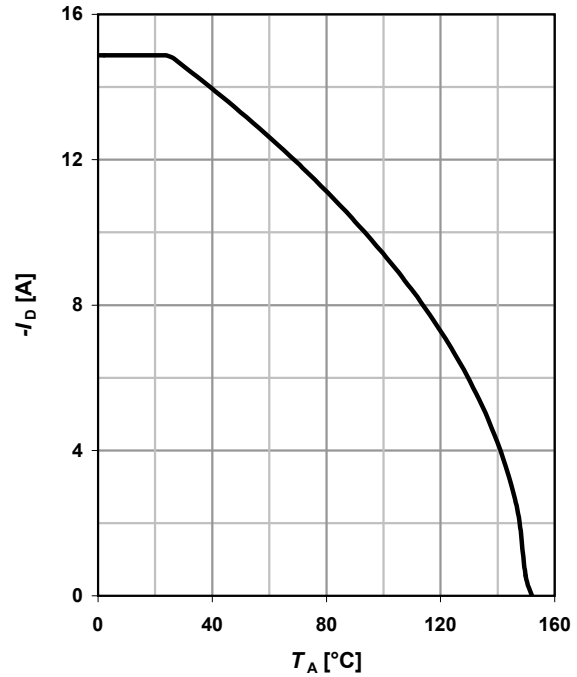
1 Power dissipation

$$P_{\text{tot}} = f(T_A); t_p \leq 10 \text{ s}$$



2 Drain current

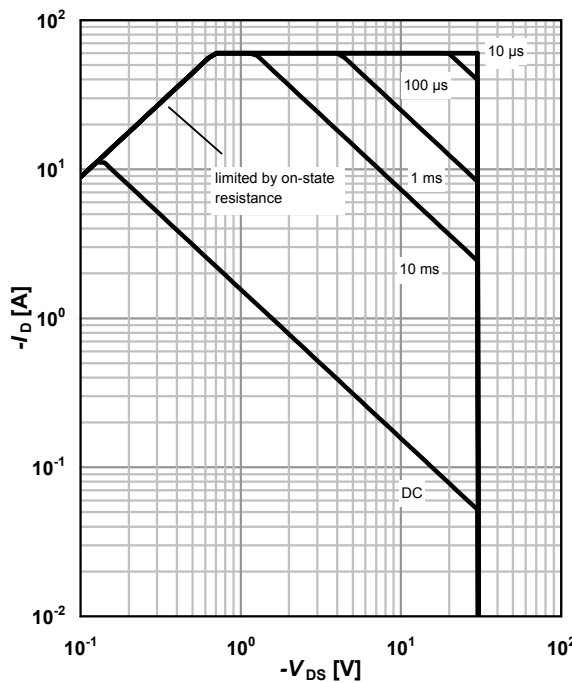
$$I_D = f(T_A); |V_{GS}| \geq 10 \text{ V}; t_p \leq 10 \text{ s}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_A = 25^\circ\text{C}^{(1)}; D = 0$$

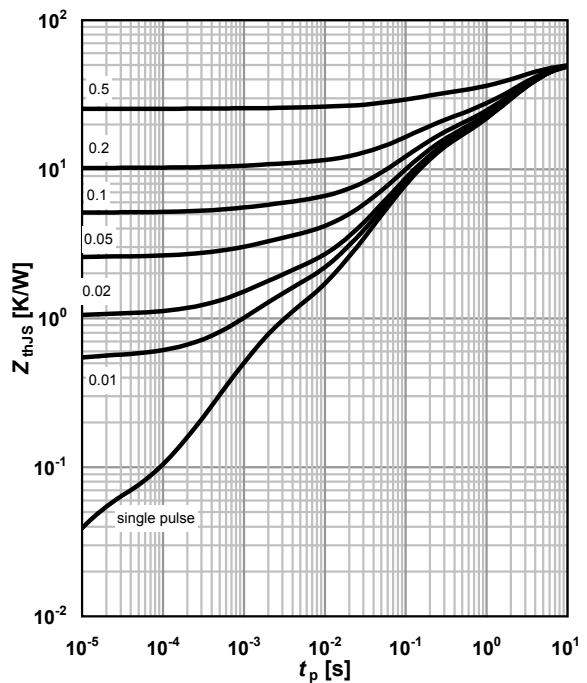
parameter: t_p



4 Max. transient thermal impedance

$$Z_{\text{thJS}} = f(t_p)$$

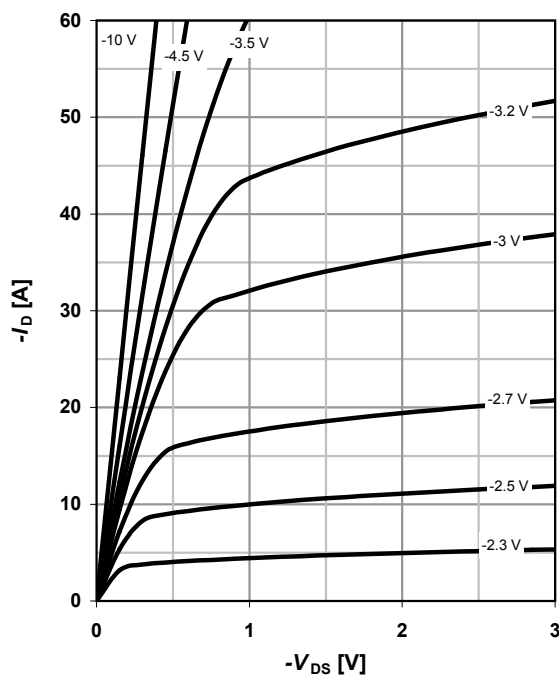
parameter: $D = t_p / T$



5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

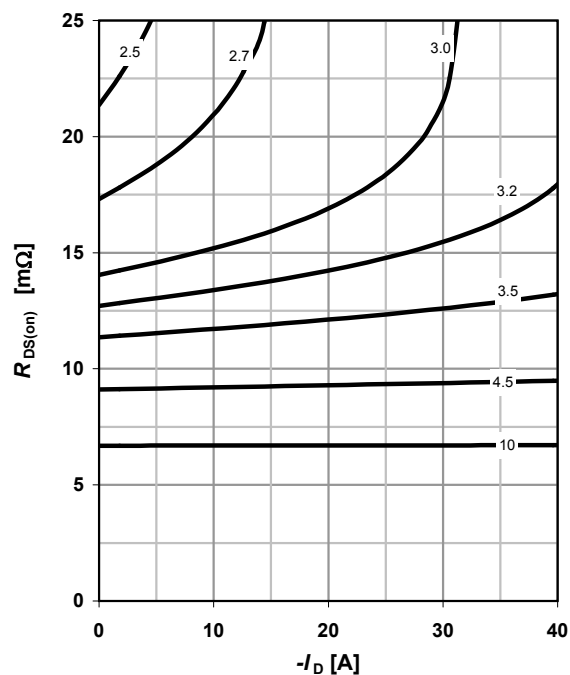
parameter: V_{GS}



6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

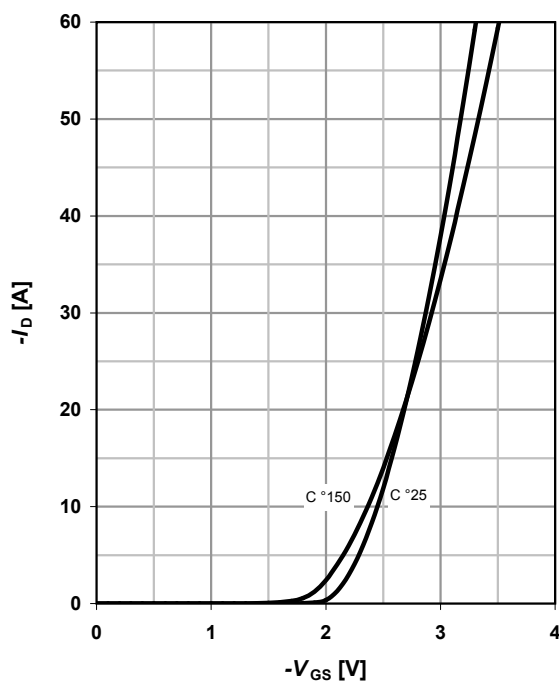
parameter: V_{GS}



7 Typ. transfer characteristics

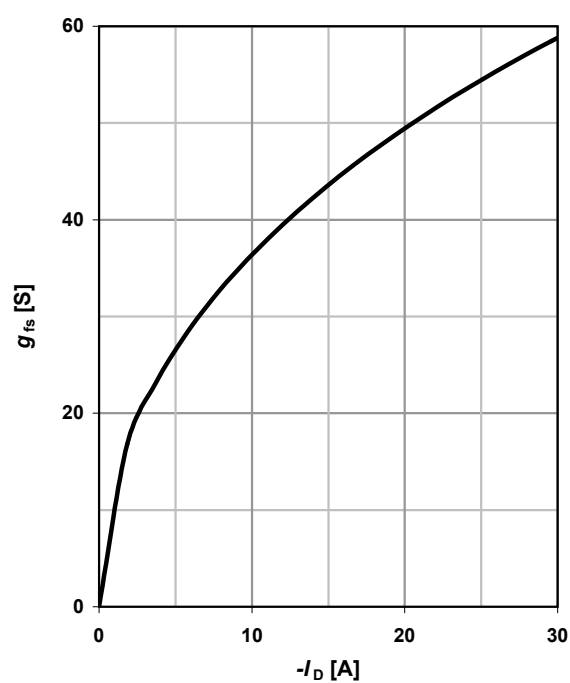
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

parameter: T_j



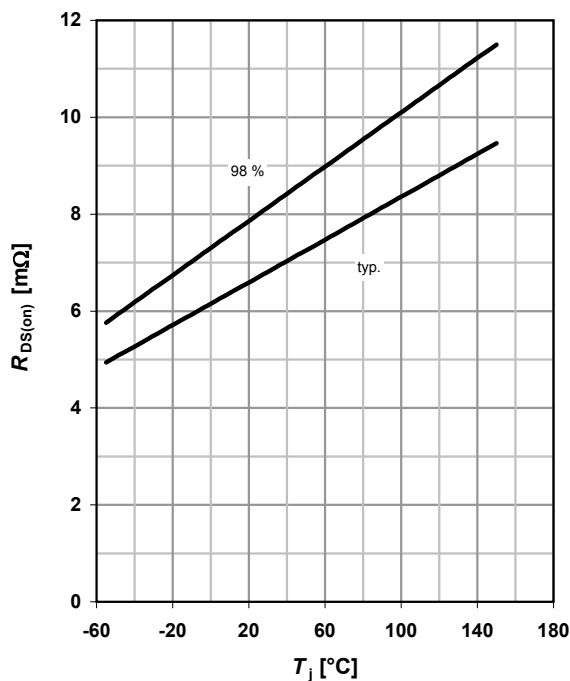
8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$



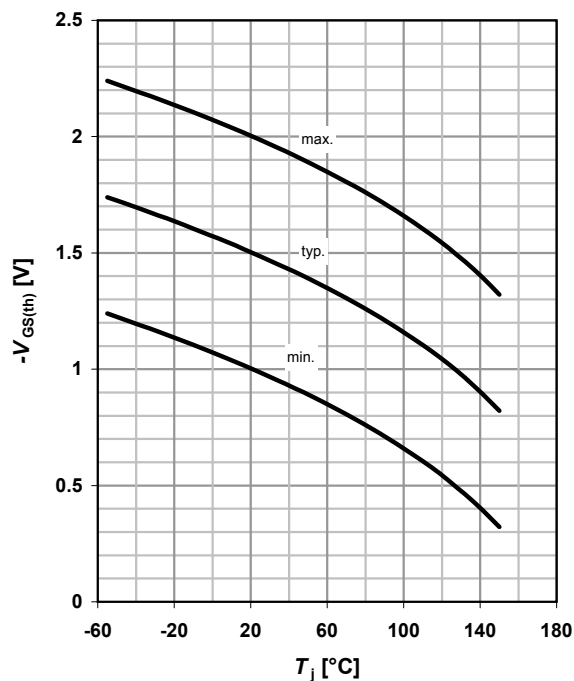
9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j); I_D = -14.9 \text{ A}; V_{GS} = -10 \text{ V}$$



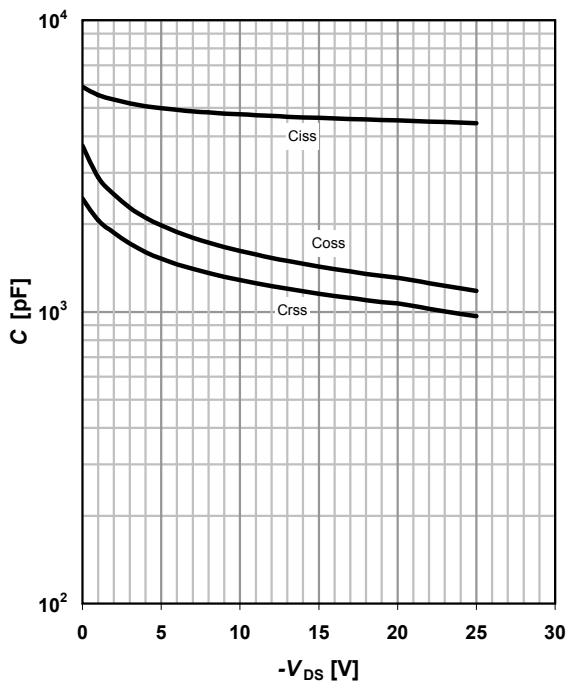
10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = -250 \text{ μA}$$



11 Typ. capacitances

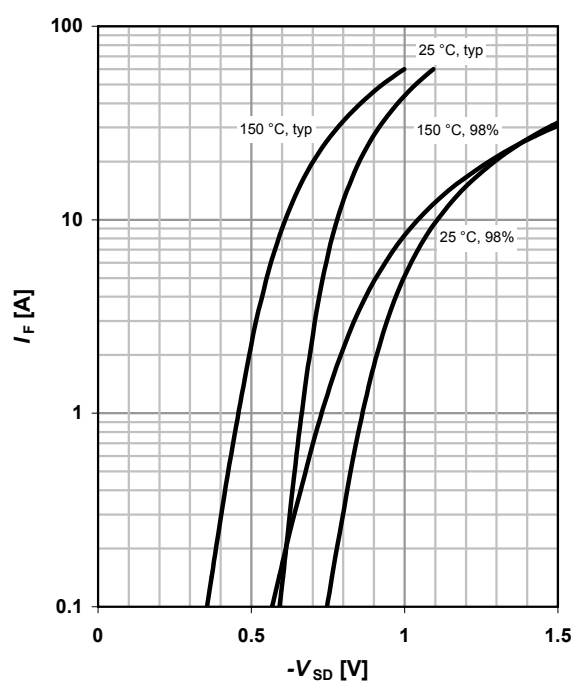
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

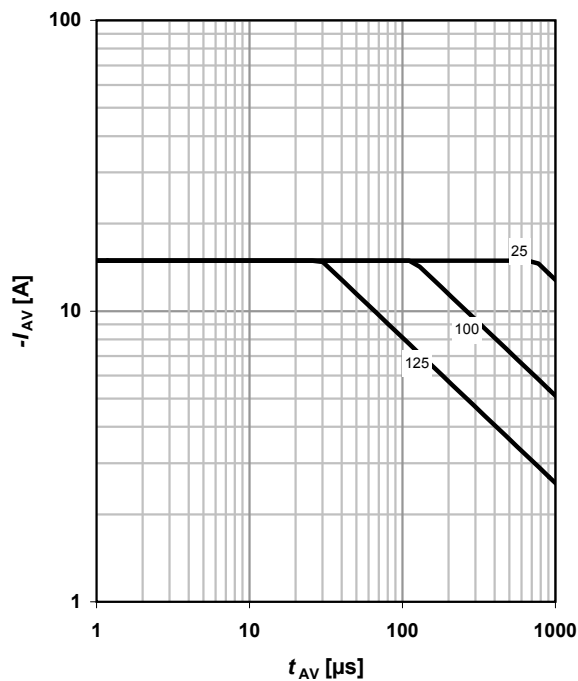
parameter: T_j



13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

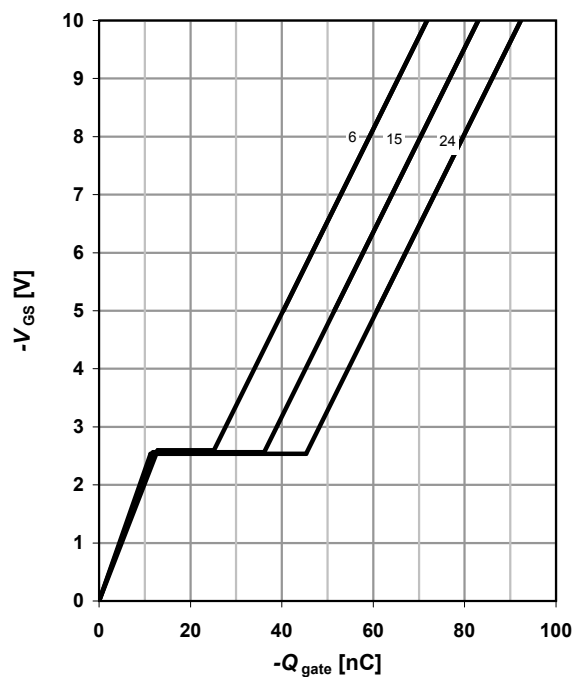
parameter: $T_{j(\text{start})}$



14 Typ. gate charge

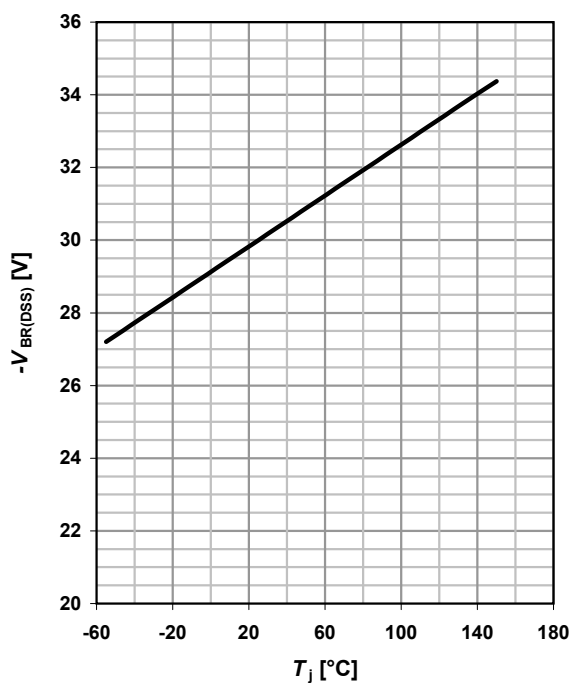
$$V_{GS}=f(Q_{\text{gate}}); I_D=-14.9\ \text{A pulsed}$$

parameter: V_{DD}

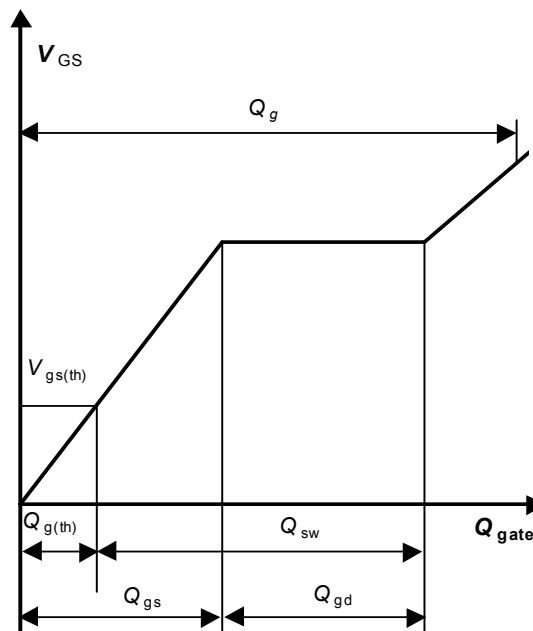


15 Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=-250\ \mu\text{A}$$

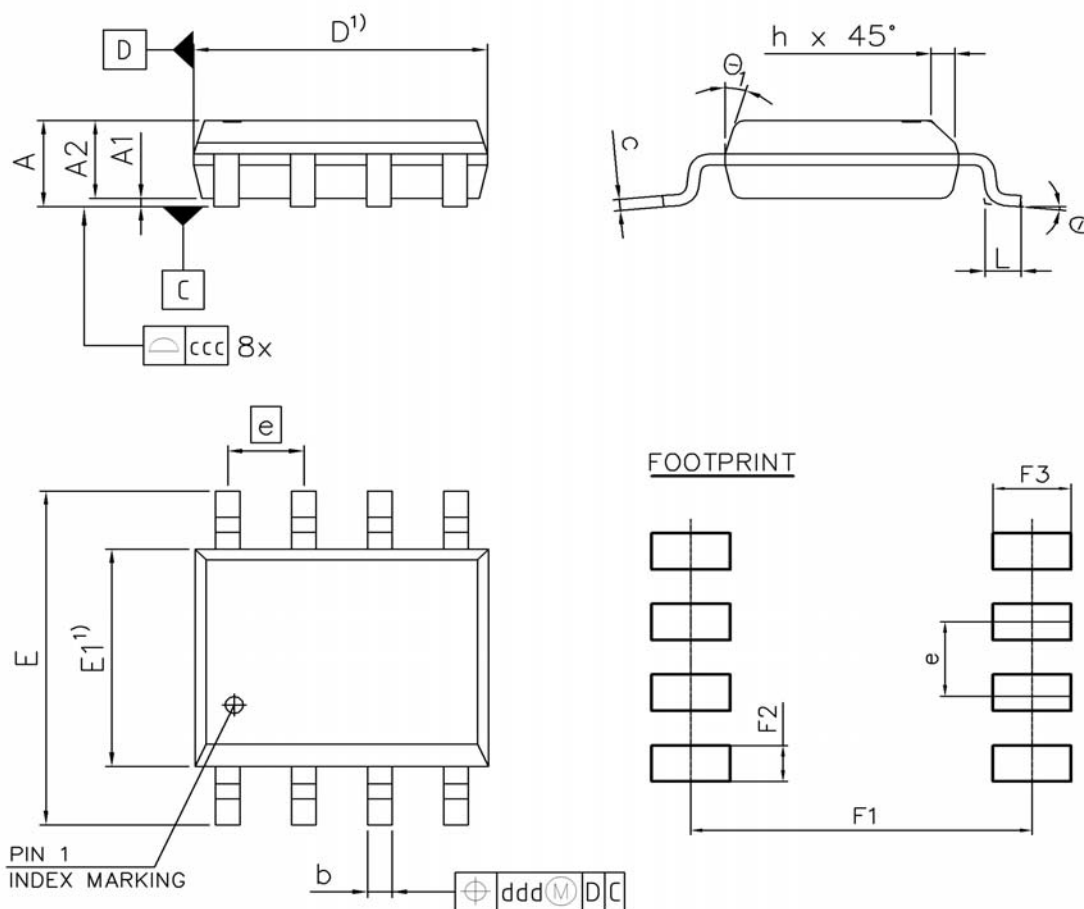


16 Gate charge waveforms



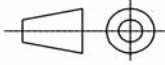
Package Outline

P-DSO-8: Outline



1) DOES NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.10	-	0.004	-
A2	1.25	1.65	0.049	0.065
b	0.35	0.51	0.014	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27		0.050	
N	8		8	
L	0.39	0.89	0.015	0.035
h	0.23	0.50	0.009	0.020
Θ	0°	8°	0°	8°
Θ_1	-	19°	-	19°
ccc	0.10		0.004	
ddd	0.25		0.010	
F1	5.59	5.79	0.220	0.228
F2	0.55	0.75	0.022	0.030
F3	1.21	1.41	0.048	0.056

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